

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|---------------------|
| - | 10 | "935776" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 17:36 |
| - | 416 | nano\$1wir\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 18:05 |
| - | 127 | nano\$1wir\$4 same semiconduct\$5 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 18:49 |
| - | 0 | 257/9-30.ccls, | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 17:01 |
| - | 3648 | 257/9-30.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 17:02 |
| - | 242 | 257/9-30.ccls. and (nano\$1wir\$5 or nano\$1tub\$5 or (quantum near (wir\$4 or line\$1))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 17:03 |
| - | 740 | (SiC or carbide\$1) with (doping or doped) with (boron or B) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 18:51 |
| - | 322 | (SiC or carbide\$1) with (doping or doped) with (boron or B) with (P or phosphorus) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 18:57 |
| - | 101 | (SiC or carbide\$1) with (doping or doped) with (boron) with (phosphorus) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 19:00 |
| - | 11 | (SiC or carbide\$1) with (doping or doped) with (boron) with (nitrogen with phosphorus) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/07 19:00 |
| - | 11 | "738793" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/08 10:48 |
| - | 972 | (si or silicon) near wire\$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/08 10:48 |
| - | 9 | ((si or silicon) near wire\$1) same dopant same phosphorus | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/08 10:50 |

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|---|----|--|---|---------------------|
| - | 31 | ((si or silicon) near wire\$1) same (dopant or doping or doped or dop) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/08 10:50 |
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